

### General Description

The WSP4067B is the highest performance trench N-ch and P-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSP4067B meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

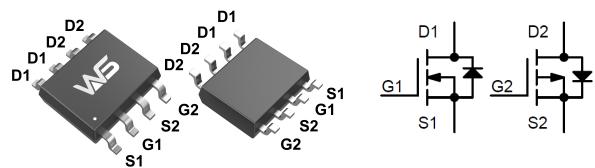
### Product Summary

BVDSS	RDSON	ID
40V	25mΩ	6.0A
-40V	40mΩ	-5.1A

### Applications

- High Frequency Point-of-Load Synchronous Buck Converter.
- Networking DC-DC Power System
- Load Switch

### SOP-8 Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
$V_{DS}$	Drain-Source Voltage	40	-40	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current	6.0	-5.1	A
$I_D@T_C=70^\circ C$	Continuous Drain Current	3.9	-3.2	A
$I_{DM}$	Pulsed Drain Current	24	-20	A
$P_D@T_C=25^\circ C$	Total Power Dissipation	2	2	W
$T_J/T_{STG}$	Operating Temperature /Storage Temperature Range	-55 to 150		$^\circ C$

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	62.5	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	50	$^\circ C/W$

**N-Channel Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.067	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =6A	---	25	35	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	---	40	55	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.0	1.6	2.2	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-5.24	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =32V, V <sub>GS</sub> =0V, T <sub>J</sub> =85°C	---	---	1	uA
		V <sub>DS</sub> =32V, V <sub>GS</sub> =0V, T <sub>J</sub> =85°C	---	---	30	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A	---	11	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	2	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	2.2	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DS</sub> = 20 V, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 3.3 Ω, R <sub>L</sub> = 3.3 Ω, I <sub>DS</sub> = 6 A.	---	1.9	---	ns
T <sub>r</sub>	Rise Time		---	18.6	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	8.7	---	
T <sub>f</sub>	Fall Time		---	2.6	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, f=1MHz	---	600	---	pF
C <sub>oss</sub>	Output Capacitance		---	62	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	48	---	

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	T <sub>A</sub> =25°C.	---	---	2.6	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =1A	---	---	1.3	V

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the t<sub>s</sub> 10s junction to ambient thermal resistance rating.

**P-Channel Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-40	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	---	-0.03	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4A	---	40	50	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A	---	55	75	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.0	-1.6	-2.2	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-32V, V <sub>GS</sub> =0V, T <sub>J</sub> =85°C	---	---	-1	uA
		V <sub>DS</sub> =-32V, V <sub>GS</sub> =0V, T <sub>J</sub> =85°C	---	---	-30	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-20V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-5.1A	---	20	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	5.7	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	4.6	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =-20V, V <sub>GS</sub> =-10V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =-5.1A, R <sub>L</sub> =3.9Ω.	---	6.8	---	ns
T <sub>r</sub>	Rise Time		---	33	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	30	---	
T <sub>f</sub>	Fall Time		---	12	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHz	---	1100	---	pF
C <sub>oss</sub>	Output Capacitance		---	100	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	80	---	

**Diode Characteristics**

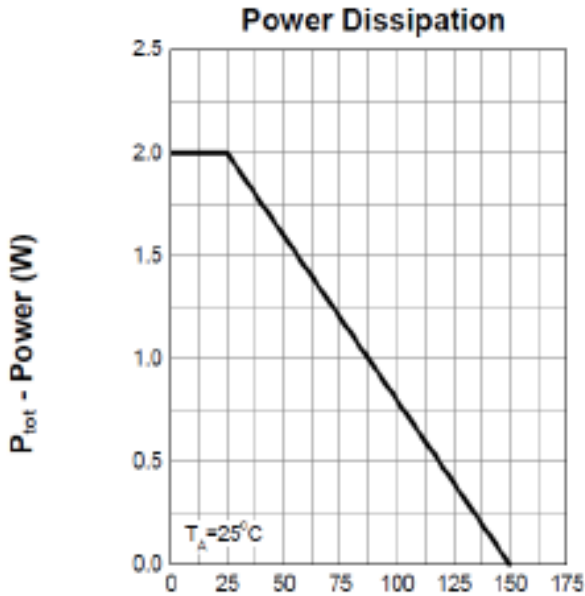
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	T <sub>A</sub> =25°C.	---	---	-2.6	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A.	---	---	-1.2	V

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any given application depends on the user's specific board design.

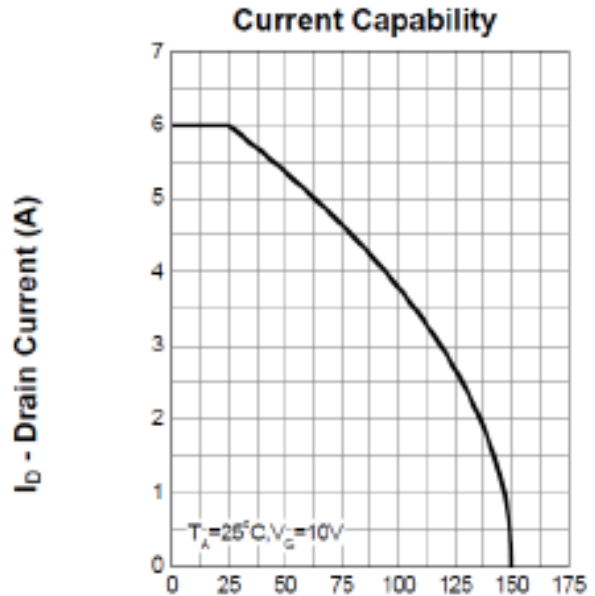
B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the t<sub>s</sub> ≤ 10s junction to ambient thermal resistance rating.

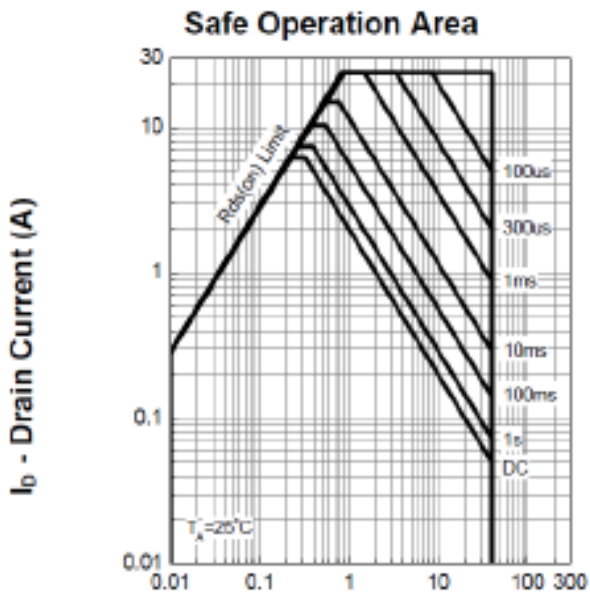
**N-Channel Typical Characteristics**



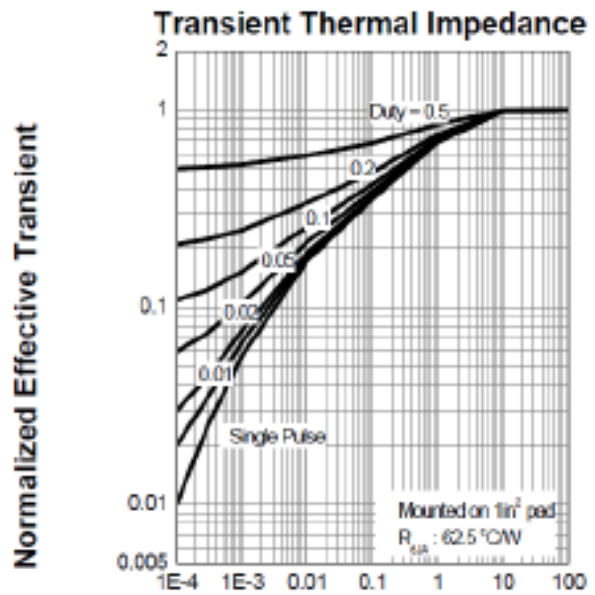
$T_j$  – Junction Temperature ( $^\circ\text{C}$ )



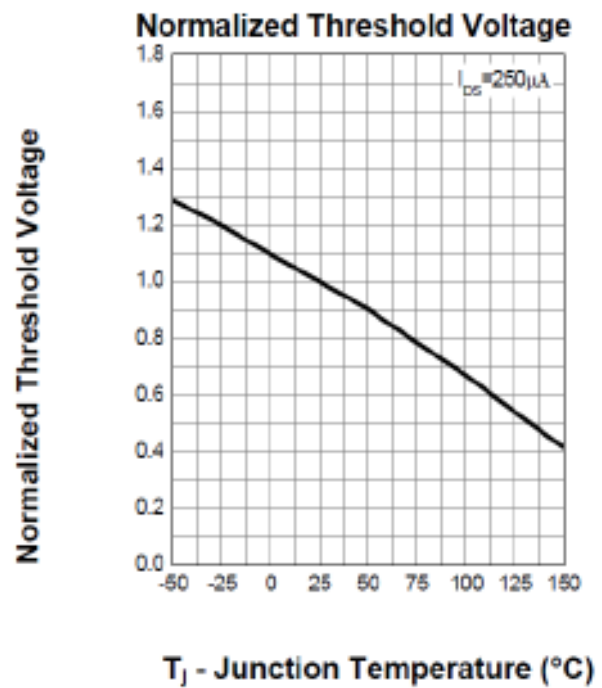
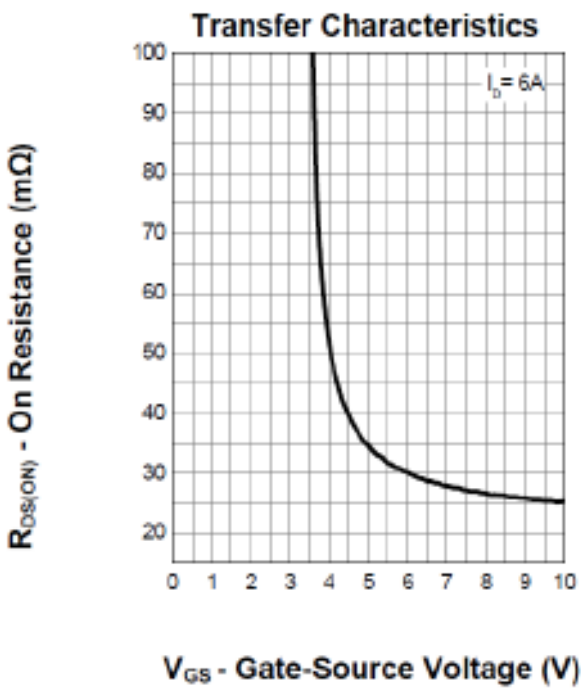
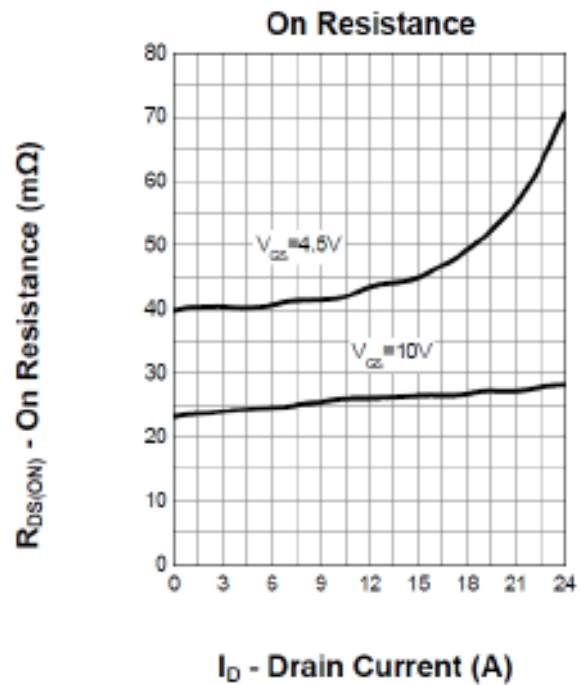
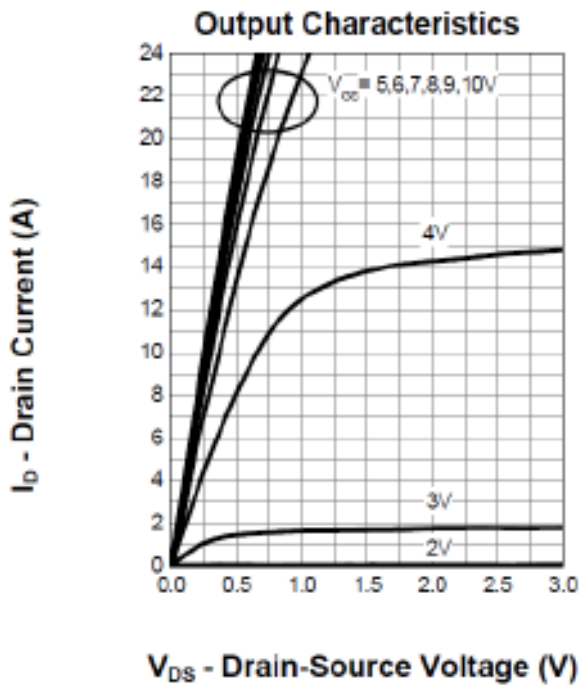
$T_j$  – Junction Temperature( $^\circ\text{C}$ )

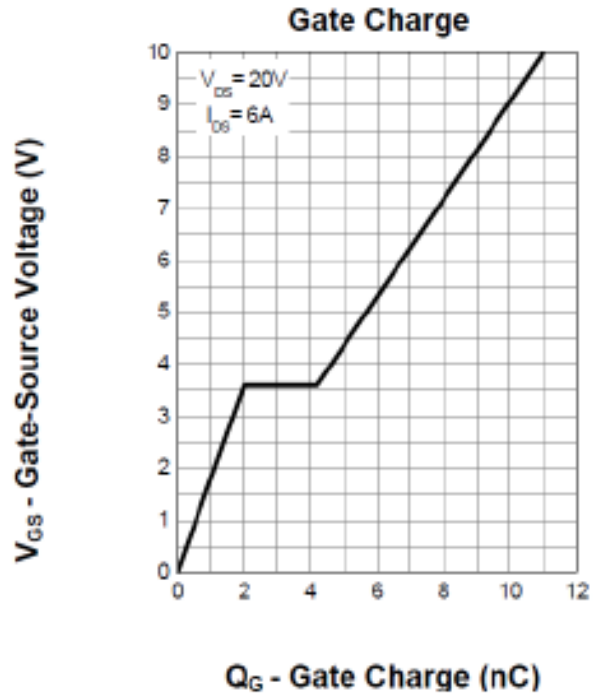
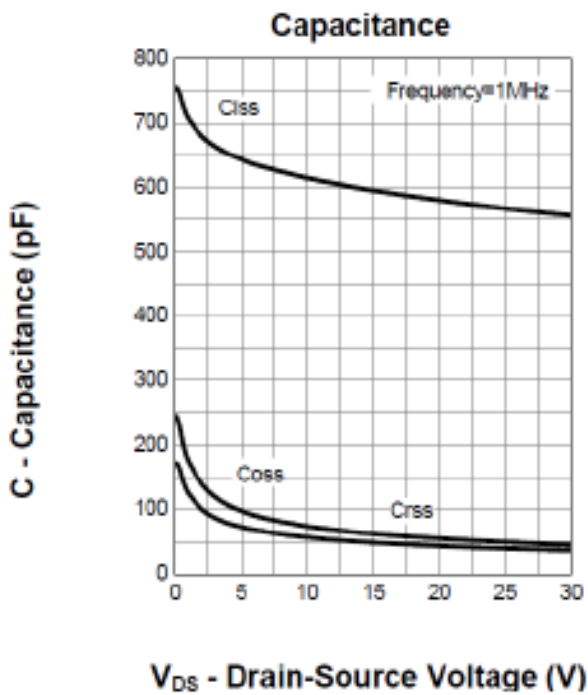
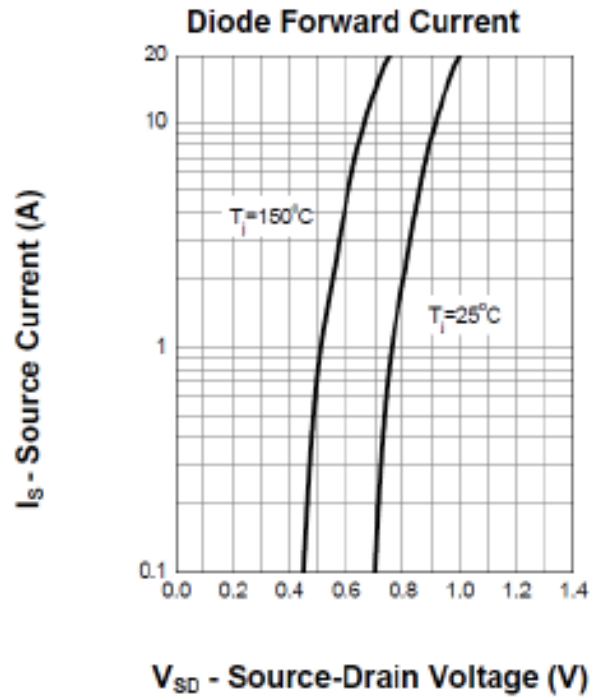
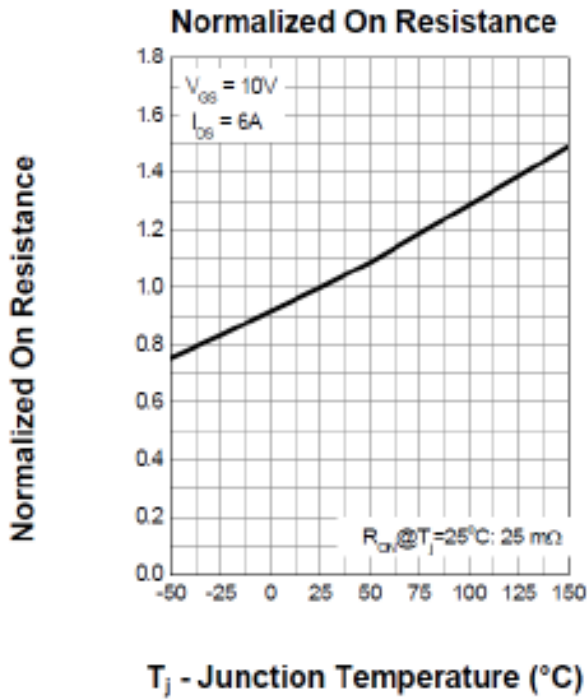


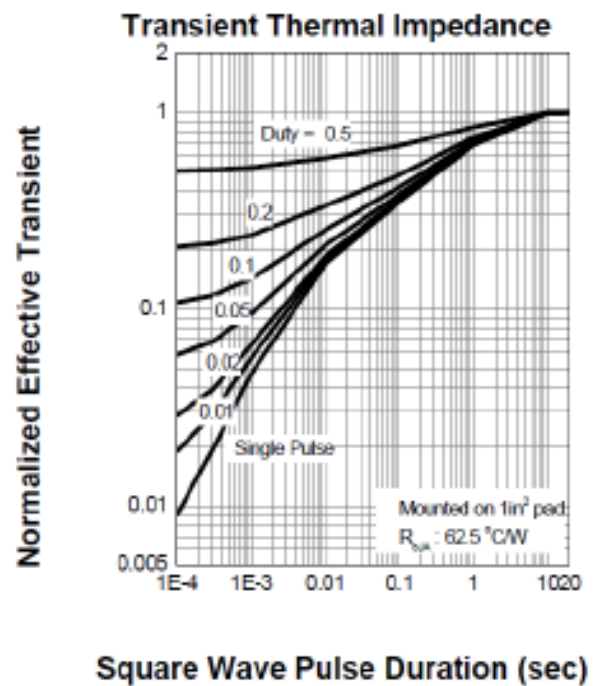
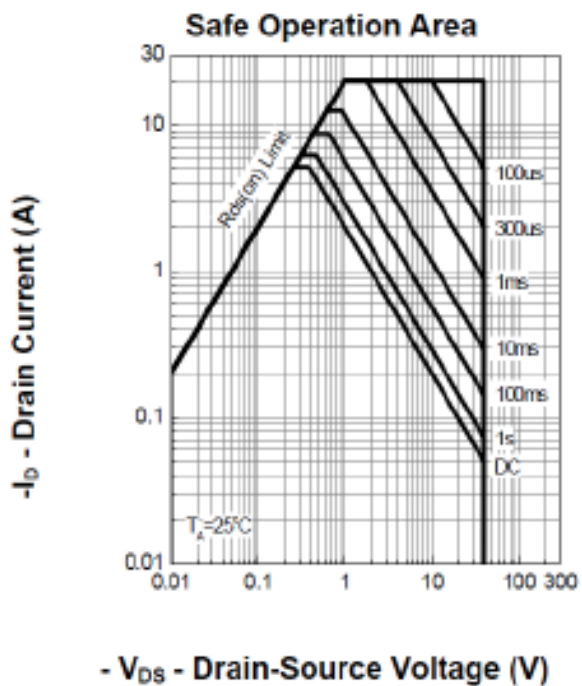
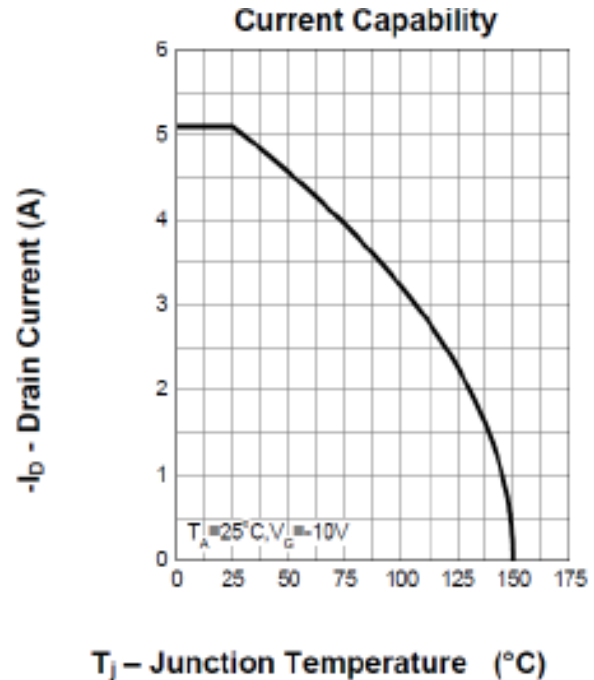
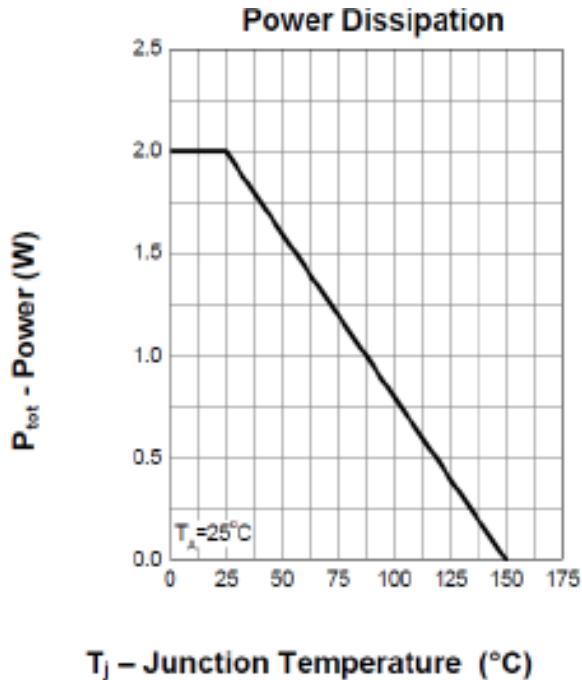
$V_{DS}$  - Drain-Source Voltage (V)



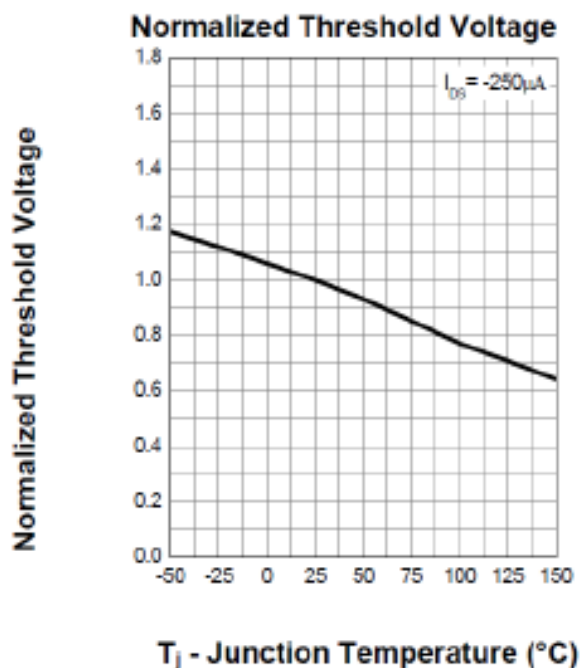
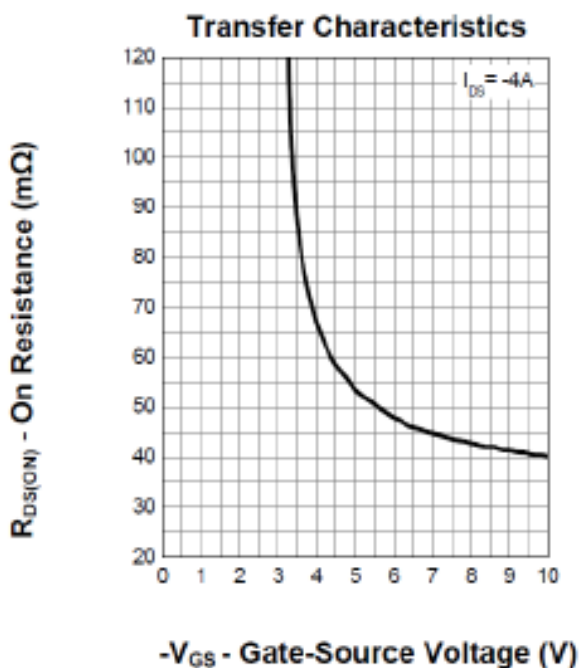
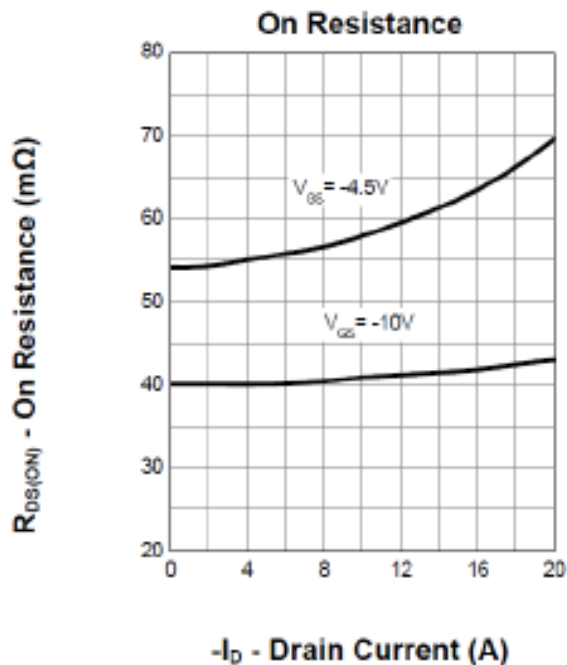
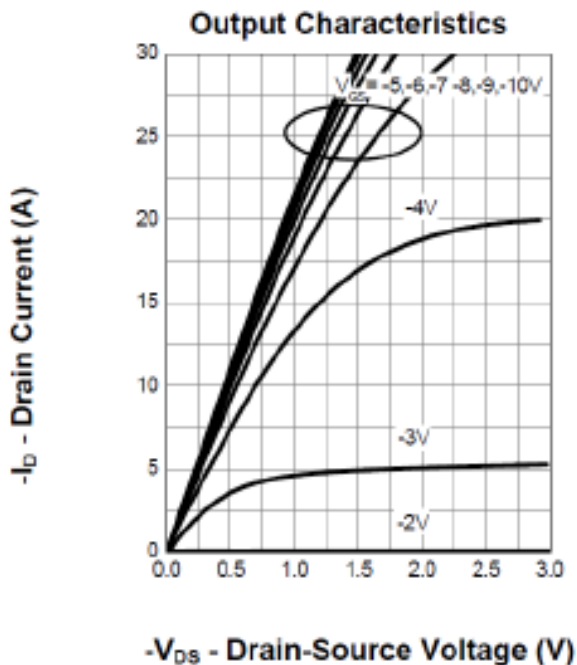
Square Wave Pulse Duration (sec)



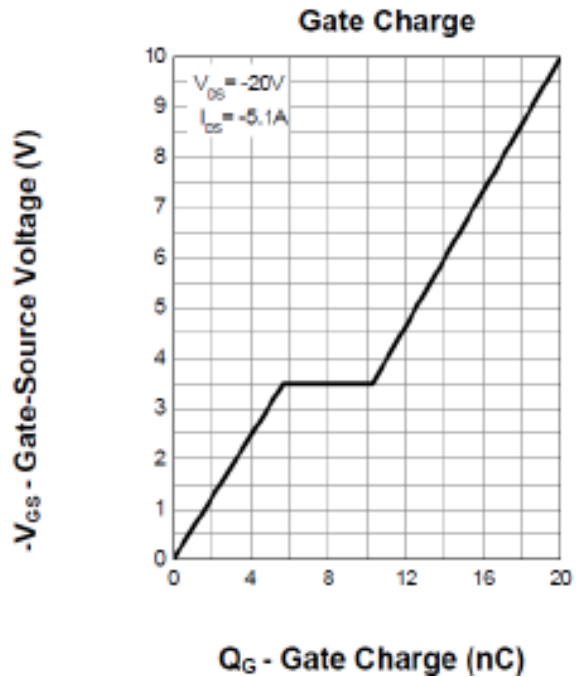
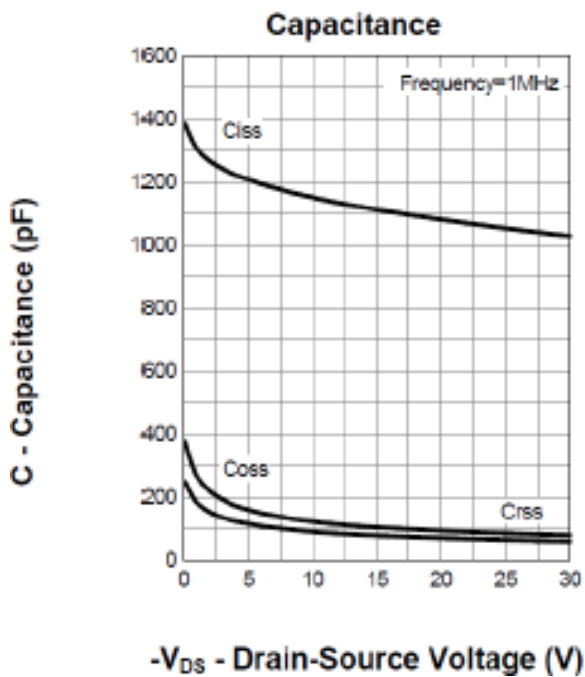
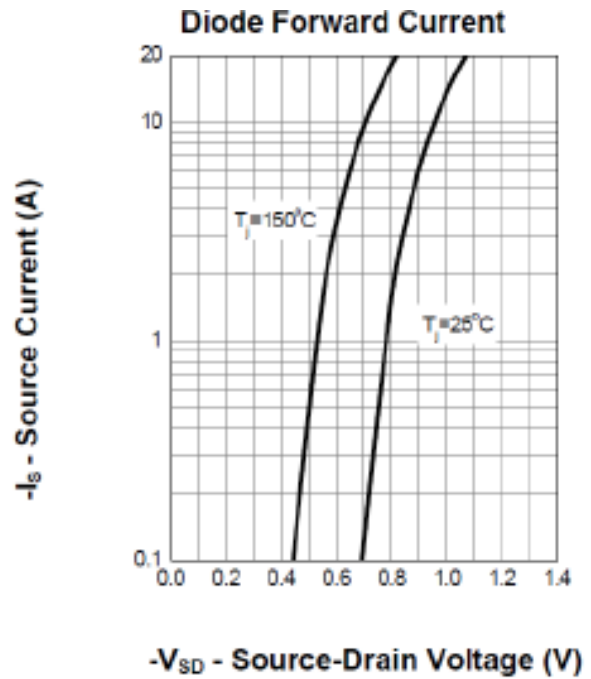
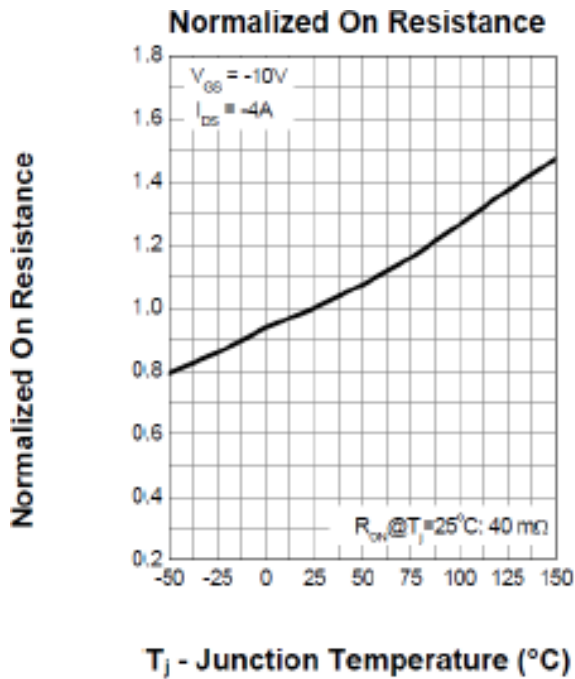














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